

Jeffrey T Glass

List of Publications by Year in descending order

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124
papers

6,347
citations

66234

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127
times ranked

4576
citing authors

#	ARTICLE	IF	CITATIONS
1	Polyethylenimine-Enhanced Electrocatalytic Reduction of CO ₂ to Formate at Nitrogen-Doped Carbon Nanomaterials. <i>Journal of the American Chemical Society</i> , 2014, 136, 7845-7848.	6.6	591
2	Analysis of the composite structures in diamond thin films by Raman spectroscopy. <i>Physical Review B</i> , 1990, 41, 3738-3745.	1.1	532
3	Textured diamond growth on (100) β -SiC via microwave plasma chemical vapor deposition. <i>Applied Physics Letters</i> , 1992, 60, 698-700.	1.5	385
4	Textured growth of diamond on silicon via nitric acid etching and bias-enhanced nucleation. <i>Applied Physics Letters</i> , 1993, 62, 1215-1217.	1.5	325
5	Characterization of diamond thin films: Diamond phase identification, surface morphology, and defect structures. <i>Journal of Materials Research</i> , 1989, 4, 373-384.	1.2	256
6	Critical evaluation of the status of the areas for future research regarding the wide band gap semiconductors diamond, gallium nitride and silicon carbide. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1988, 1, 77-104.	1.7	227
7	Chemical vapor deposition and characterization of β -SiC thin films on off-axis β -SiC substrates. <i>Journal of Applied Physics</i> , 1988, 64, 2672-2679.	1.1	213
8	Material and electrical characterization of polycrystalline boron-doped diamond films grown by microwave plasma chemical vapor deposition. <i>Journal of Applied Physics</i> , 1991, 69, 3142-3148.	1.1	149
9	Correlation of the electrical properties of metal contacts on diamond films with the chemical nature of the metal-diamond interface. II. Titanium contacts: A carbide-forming metal. <i>Physical Review B</i> , 1992, 45, 11975-11981.	1.1	136
10	The origin of the broadband luminescence and the effect of nitrogen doping on the optical properties of diamond films. <i>Journal of Applied Physics</i> , 1994, 76, 3020-3027.	1.1	129
11	Oriented diamond films grown on nickel substrates. <i>Applied Physics Letters</i> , 1993, 63, 1640-1642.	1.5	109
12	Epitaxial nucleation of diamond on β -SiC via bias-enhanced microwave plasma chemical vapor deposition. <i>Diamond and Related Materials</i> , 1993, 2, 142-146.	1.8	103
13	An examination of double positioning boundaries and interface misfit in β -SiC films on α -SiC substrates. <i>Journal of Applied Physics</i> , 1988, 63, 2645-2650.	1.1	94
14	Electron emission from diamond coated silicon field emitters. <i>Applied Physics Letters</i> , 1994, 65, 2842-2844.	1.5	93
15	The Effect of Metallurgical Variables on the Electrocatalytic Properties of PtCr Alloys. <i>Journal of the Electrochemical Society</i> , 1987, 134, 58-65.	1.3	92
16	Growth rate, surface morphology, and defect microstructures of β -SiC films chemically vapor deposited on β -SiC substrates. <i>Journal of Materials Research</i> , 1989, 4, 204-214.	1.2	91
17	Twinning and faceting in early stages of diamond growth by chemical vapor deposition. <i>Journal of Materials Research</i> , 1992, 7, 3001-3009.	1.2	90
18	Microphotoluminescence and Raman scattering study of defect formation in diamond films. <i>Journal of Applied Physics</i> , 1993, 73, 3951-3957.	1.1	89

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19	Nucleation of oriented diamond films on nickel substrates. <i>Journal of Materials Research</i> , 1993, 8, 1773-1776.	1.2	84
20	Oriented nucleation and growth of diamond films on SiC and Si. <i>Applied Physics Letters</i> , 1993, 63, 1792-1794.	1.5	84
21	<i>In situ</i> growth rate measurement and nucleation enhancement for microwave plasma CVD of diamond. <i>Journal of Materials Research</i> , 1992, 7, 257-260.	1.2	80
22	Solution-Processed, Antimony-Doped Tin Oxide Colloid Films Enable High-Performance TiO_2 Photoanodes for Water Splitting. <i>Nano Letters</i> , 2013, 13, 1481-1488.	4.5	79
23	Diamond and SiC heteroepitaxial interfaces: A theoretical and experimental study. <i>Physical Review B</i> , 1993, 47, 6529-6542.	1.1	78
24	Epitaxial growth of SiC thin films on SiC substrates via chemical vapor deposition. <i>Applied Physics Letters</i> , 1986, 49, 1074-1076.	1.5	75
25	Large-area mosaic diamond films approaching single-crystal quality. <i>Applied Physics Letters</i> , 1991, 58, 2485-2487.	1.5	74
26	Field emission characteristics of diamond coated silicon field emitters. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1995, 13, 422.	1.6	71
27	Electron microscopy of vapor phase deposited diamond. <i>Journal of Materials Research</i> , 1990, 5, 801-810.	1.2	68
28	Three-dimensional arrays of graphenated carbon nanotubes. <i>Journal of Materials Research</i> , 2012, 27, 1046-1053.	1.2	67
29	A review of the electrical characteristics of metal contacts on diamond. <i>Thin Solid Films</i> , 1992, 212, 19-24.	0.8	65
30	Electrical Contacts to Beta Silicon Carbide Thin Films. <i>Journal of the Electrochemical Society</i> , 1988, 135, 359-362.	1.3	63
31	On-chip electron-impact ion source using carbon nanotube field emitters. <i>Applied Physics Letters</i> , 2007, 90, 124102.	1.5	61
32	Nothing is like a vacuum. <i>Nature Nanotechnology</i> , 2012, 7, 485-487.	15.6	55
33	Nucleation and selected area deposition of diamond by biased hot filament chemical vapor deposition. <i>Journal of Materials Research</i> , 1995, 10, 425-430.	1.2	54
34	Effects of boron doping on the surface morphology and structural imperfections of diamond films. <i>Diamond and Related Materials</i> , 1992, 1, 828-835.	1.8	53
35	Vapor deposition of diamond thin films on various substrates. <i>Applied Physics Letters</i> , 1990, 57, 1916-1918.	1.5	52
36	Correlation of the electrical properties of metal contacts on diamond films with the chemical nature of the metal-diamond interface. I. Gold contacts: A non-carbide-forming metal. <i>Physical Review B</i> , 1992, 45, 11968-11974.	1.1	51

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37	Graphenated carbon nanotubes for enhanced electrochemical double layer capacitor performance. Applied Physics Letters, 2011, 99, 183104.	1.5	49
38	Electron microscopic characterization of diamond films grown on Si by bias-controlled chemical vapor deposition. Journal of Materials Research, 1990, 5, 2367-2377.	1.2	48
39	Temperature dependence of the current-voltage characteristics of metal-semiconductor field-effect transistors in n-type SiC grown via chemical vapor deposition. Applied Physics Letters, 1987, 51, 442-444.	1.5	47
40	Fabrication of diamond thin-film thermistors for high-temperature applications. Diamond and Related Materials, 1993, 2, 816-819.	1.8	47
41	Bias induced diamond nucleation studies on refractory metal substrates. Journal of Applied Physics, 1995, 77, 5119-5124.	1.1	46
42	Nucleation of oriented diamond particles on cobalt substrates. Journal of Applied Physics, 1995, 78, 1291-1296.	1.1	43
43	Growth of vertically aligned bamboo-like carbon nanotubes from ammonia/methane precursors using a platinum catalyst. Carbon, 2011, 49, 266-274.	5.4	43
44	Organizational designs for R&D. Academy of Management Perspectives, 2002, 16, 55-66.	4.3	42
45	Bias-enhanced nucleation of highly oriented diamond on titanium carbide (111) substrates. Applied Physics Letters, 1995, 66, 2810-2812.	1.5	39
46	Bias-controlled chemical vapor deposition of diamond thin films. Applied Physics Letters, 1990, 56, 620-622.	1.5	38
47	The analysis of defect structures and substrate/film interfaces of diamond thin films. Journal of Crystal Growth, 1990, 99, 1168-1176.	0.7	37
48	The Effect of Phosphoric Acid Concentration on Electrocatalysis. Journal of the Electrochemical Society, 1989, 136, 656-660.	1.3	36
49	Observation of surface modification and nucleation during deposition of diamond on silicon by scanning tunneling microscopy. Journal of Applied Physics, 1991, 69, 6400-6405.	1.1	35
50	Verification of the $\text{O}=\text{Si}=\text{N}$ complex in plasma-enhanced chemical vapor deposition silicon oxynitride films. Applied Physics Letters, 2005, 87, 261907.	1.5	35
51	A method to obtain a Ragone plot for evaluation of carbon nanotube supercapacitor electrodes. Journal of Materials Research, 2010, 25, 1500-1506.	1.2	35
52	Selected topics on the synthesis, properties and applications of multiwalled carbon nanotubes. Diamond and Related Materials, 2014, 42, 49-57.	1.8	34
53	Diamond nucleation and growth on reactive transition-metal substrates. Journal of Materials Research, 1995, 10, 1455-1460.	1.2	32
54	Carbon nanostructures: A morphological classification for charge density optimization. Diamond and Related Materials, 2012, 23, 130-134.	1.8	30

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55	Enhanced electron transfer kinetics through hybrid graphene-carbon nanotube films. <i>Electrochemistry Communications</i> , 2014, 48, 103-106.	2.3	29
56	Diamond nucleation on nickel substrates seeded with non-diamond carbon. <i>Journal of Materials Research</i> , 1994, 9, 1063-1066.	1.2	28
57	Analysis via transmission electron microscopy of the quality of diamond films deposited from the vapor phase. <i>Diamond and Related Materials</i> , 1991, 1, 25-32.	1.8	26
58	Alloying Effects of Cosputtered Gold-Platinum Thin Films on the Oxygen Reduction Reaction in Acidic Electrolyte. <i>Journal of the Electrochemical Society</i> , 2008, 155, B852.	1.3	25
59	Effect of surface hydrogen on metal-diamond interface properties. <i>Journal of Applied Physics</i> , 1993, 73, 835-842.	1.1	24
60	Integrated Flexible Conversion Circuit between a Flexible Photovoltaic and Supercapacitors for Powering Wearable Sensors. <i>Journal of the Electrochemical Society</i> , 2018, 165, B3122-B3129.	1.3	23
61	The effect of substrate material on bias-enhanced diamond nucleation. <i>Diamond and Related Materials</i> , 1994, 3, 1188-1195.	1.8	22
62	The effects of structure, composition, and chemical bonding on the mechanical properties of Si-aC:H thin films. <i>Surface and Coatings Technology</i> , 2002, 157, 197-206.	2.2	22
63	Effects of argon presputtering on the formation of aluminum contacts on polycrystalline diamond. <i>Journal of Applied Physics</i> , 1992, 72, 5912-5918.	1.1	21
64	Diamond deposition using a planar radio frequency inductively coupled plasma. <i>Applied Physics Letters</i> , 1995, 66, 3579-3581.	1.5	20
65	Influence of Deposition Parameters on the Composition and Structure of Reactively Sputtered Nanocomposite TaC/a-C:H Thin Films. <i>Journal of Materials Research</i> , 2005, 20, 2583-2596.	1.2	19
66	Intellectual property (IP) management: organizational processes and structures, and the role of IP donations. <i>Journal of Technology Transfer</i> , 2008, 33, 549-559.	2.5	19
67	Effect of porosity variation on the electrochemical behavior of vertically aligned multi-walled carbon nanotubes. <i>Electrochemistry Communications</i> , 2012, 19, 138-141.	2.3	19
68	Growth of diamond films using an enclosed combustion flame. <i>Journal of Applied Physics</i> , 1995, 78, 4144-4156.	1.1	18
69	Comparison of silicon, nickel, and nickel silicide (Ni ₃ Si) as substrates for epitaxial diamond growth. <i>Surface Science</i> , 1995, 334, 179-194.	0.8	18
70	The formation of epitaxial hexagonal boron nitride on nickel substrates. <i>Journal of Electronic Materials</i> , 2005, 34, 1558-1564.	1.0	18
71	Measurement of reactive and condensable gas permeation using a mass spectrometer. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2008, 26, 1128-1137.	0.9	18
72	Electrical conductivity and photoluminescence of diamond films grown by downstream microwave plasma CVD. <i>Journal of Electronic Materials</i> , 1992, 21, 629-634.	1.0	17

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73	Correlation of interface chemistry to electrical properties of metal contacts on diamond. <i>Diamond and Related Materials</i> , 1993, 2, 963-969.	1.8	17
74	High Knudsen number fluid flow at near-standard temperature and pressure conditions using precision nanochannels. <i>Microfluidics and Nanofluidics</i> , 2011, 10, 425-433.	1.0	17
75	Combustion growth of large diamond crystals. <i>Journal of Crystal Growth</i> , 1993, 129, 45-55.	0.7	16
76	Improved uniformity and selected area deposition of diamond by the oxy-acetylene flame method. <i>Journal of Materials Research</i> , 1992, 7, 2144-2150.	1.2	15
77	Perspectives on the Growth of High Edge Density Carbon Nanostructures: Transitions from Vertically Oriented Graphene Nanosheets to Graphenated Carbon Nanotubes. <i>Journal of Physical Chemistry C</i> , 2014, 118, 16126-16132.	1.5	15
78	The effect of gold on platinum oxidation in homogeneous Au-Pt electrocatalysts. <i>Applied Surface Science</i> , 2010, 257, 1431-1436.	3.1	14
79	Investigation of the low angle grain boundaries in highly oriented diamond films via transmission electron microscopy. <i>Journal of Materials Research</i> , 1994, 9, 2487-2489.	1.2	13
80	Investigation of the process factor space on bias-enhanced nucleation of diamond on silicon. <i>Thin Solid Films</i> , 1995, 261, 4-11.	0.8	13
81	The effects of thermal annealing on the microstructural, optical and electrical properties of beta silicon carbide films implanted with boron or nitrogen. <i>Journal of Electronic Materials</i> , 1989, 18, 157-165.	1.0	12
82	The role of geometric considerations in the diamond-cubic boron nitride heteroepitaxial system. <i>Journal of Applied Physics</i> , 1991, 69, 2679-2681.	1.1	12
83	High voltage microelectromechanical systems platform for fully integrated, on-chip, vacuum electronic devices. <i>Applied Physics Letters</i> , 2008, 92, 224101.	1.5	12
84	Titanium carbide rectifying contacts on boron-doped polycrystalline diamond. <i>Diamond and Related Materials</i> , 1993, 2, 37-40.	1.8	11
85	The Electrochemical Stability and Calculated Free Energies of PtCr Alloys. <i>Journal of the Electrochemical Society</i> , 1988, 135, 1650-1658.	1.3	10
86	High sensitivity permeation measurement system for ultrabARRIER thin films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2007, 25, 1587-1593.	0.9	10
87	Microfabrication of diamond films: selective deposition and etching. <i>Surface and Coatings Technology</i> , 1991, 47, 465-473.	2.2	9
88	Effects of applied substrate bias during reactive sputter deposition of nanocomposite tantalum carbide/amorphous hydrocarbon thin films. <i>Thin Solid Films</i> , 2007, 515, 5403-5410.	0.8	9
89	Compressive Mass Analysis on Quadrupole Ion Trap Systems. <i>Journal of the American Society for Mass Spectrometry</i> , 2014, 25, 1295-1304.	1.2	9
90	Electron Microscopy of Defects in Epitaxial beta-SiC Thin Films Grown on Silicon and Carbon {0001} Faces of alpha-SiC Substrates. <i>Journal of the American Ceramic Society</i> , 1990, 73, 1283-1288.	1.9	8

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91	Effect of Substrate Orientation on Interfacial and Bulk Character of Chemically Vapor Deposited Monocrystalline Silicon Carbide Thin Films. <i>Journal of the American Ceramic Society</i> , 1990, 73, 1289-1296.	1.9	7
92	Nucleation and growth of diamond using a computer-controlled oxy-acetylene torch. <i>Diamond and Related Materials</i> , 1993, 2, 438-442.	1.8	7
93	Relationships between the thermal stability, friction, and wear properties of reactively sputtered Si ₃ N ₄ thin films. <i>Journal of Materials Research</i> , 2002, 17, 2888-2896.	1.2	7
94	Radial distribution function analyses of amorphous carbon thin films containing various levels of silicon and hydrogen. <i>Journal of Applied Physics</i> , 2004, 96, 273-279.	1.1	7
95	Analysis of 3-panel and 4-panel microscale ionization sources. <i>Journal of Applied Physics</i> , 2010, 107, .	1.1	7
96	Carbon Nanotube Electron Ionization Source for Portable Mass Spectrometry. <i>Analytical Chemistry</i> , 2011, 83, 6527-6531.	3.2	7
97	Effect of native SiO ₂ layer on the nucleation of diamond using a combustion flame. <i>Diamond and Related Materials</i> , 1994, 3, 239-244.	1.8	6
98	Mechanical property development in reactively sputtered tantalum carbide/amorphous hydrocarbon thin films. <i>Journal of Materials Research</i> , 2006, 21, 1500-1511.	1.2	6
99	Diamond surface functionalization with biomimicry – Amine surface tether and thiol moiety for electrochemical sensors. <i>Applied Surface Science</i> , 2014, 301, 293-299.	3.1	6
100	Geometric modeling of the diamond- ¹² -SiC heteroepitaxial interface. <i>Diamond and Related Materials</i> , 1993, 2, 590-596.	1.8	5
101	Simulation and testing of a lateral, microfabricated electron-impact ion source. <i>Applied Physics Letters</i> , 2009, 94, 044109.	1.5	5
102	In-Vacuo Surface Analytical Study of Diamond Nucleation on Copper Vs. Silicon. <i>Materials Research Society Symposia Proceedings</i> , 1992, 270, 347.	0.1	4
103	A Novel Ion Source and Detector for a Miniature Mass Spectrometer. , 2007, , .		4
104	A Bipolar Vacuum Microelectronic Device. <i>IEEE Transactions on Electron Devices</i> , 2011, 58, 3189-3194.	1.6	4
105	Electrochemical Charge Storage Properties of Vertically Aligned Carbon Nanotube Films: Effects of Thermal Oxidation. <i>Journal of Physical Chemistry C</i> , 2012, 116, 19526-19534.	1.5	4
106	High voltage MEMS platform for fully integrated, on-chip, vacuum electronic devices. , 2008, , .		3
107	Electrochemical Charge Storage Properties of Vertically Aligned Carbon Nanotube Films: The Activation-Enhanced Length Effect. <i>Journal of the Electrochemical Society</i> , 2011, 158, K217.	1.3	3
108	Tem Analysis of the Observed Phases During the Growth of Oriented Diamond on Nickel Substrates. <i>Materials Research Society Symposia Proceedings</i> , 1996, 423, 457.	0.1	2

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109	Effect of film chemistry on refractive index of plasma-enhanced chemical vapor deposited silicon oxynitride films: A correlative study. <i>Journal of Materials Research</i> , 2008, 23, 1433-1442.	1.2	2
110	Early Nucleation of Diamond in a Combustion Flame. <i>Materials Research Society Symposia Proceedings</i> , 1992, 270, 323.	0.1	1
111	Diamond Growth in an Oxy-Acetylene Flame by an Alternating Gas Ratio Technique. <i>Materials Research Society Symposia Proceedings</i> , 1992, 270, 329.	0.1	1
112	Electrical Conductivity as a Function of Temperature of Diamond films Grown by Downstream Microwave Plasma Chemical Vapor Deposition. <i>Materials Research Society Symposia Proceedings</i> , 1992, 270, 413.	0.1	1
113	Preface to the Proceedings of the 6th European Conference on Diamond, Diamond-like and Related Materials (Diamond Films '95), Barcelona, Spain, September 10-15, 1995. <i>Diamond and Related Materials</i> , 1996, 5, xv.	1.8	1
114	Nucleation and Growth of Oriented Diamond Films on Nickel Substrates. <i>Materials Research Society Symposia Proceedings</i> , 1996, 423, 281.	0.1	1
115	High current density electron emission from an electrodeposited metal nanowire array. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2020, 38, 043204.	0.6	1
116	Properties and applications of vapor grown diamond. <i>Carbon</i> , 1990, 28, 756-757.	5.4	0
117	Determination of impurity dopant distributions in diamond films by SIMS. <i>Carbon</i> , 1990, 28, 801.	5.4	0
118	Pulsed Laser Deposition of CdTe, HgCdTe, and SiC Thin Films on Silicon. <i>Materials Research Society Symposia Proceedings</i> , 1992, 268, 235.	0.1	0
119	Preface to the Proceedings of the 7th European Conference on Diamond, Diamond-Like and Related Materials (Diamond Films '96), Tours, France, September 8-13, 1996. <i>Diamond and Related Materials</i> , 1997, 6, xi.	1.8	0
120	High Voltage Compatible Micromachined Vacuum Electronic Devices with Carbon Nanotube Cold Cathodes. , 0, , .		0
121	Development of a Micro Mass Spectrometer: Analysis of Particle Behavior in MEMS Ion Lens Systems. <i>Microscopy and Microanalysis</i> , 2009, 15, 242-243.	0.2	0
122	Modeling Operational Modes of a Bipolar Vacuum Microelectronic Device. <i>IEEE Electron Device Letters</i> , 2012, 33, 1498-1500.	2.2	0
123	Decoration of Graphenated Carbon Nanotube Electrodes with Platinum Nanoparticles via Atomic Layer Deposition. <i>ECS Meeting Abstracts</i> , 2021, MA2021-02, 527-527.	0.0	0
124	(Digital Presentation) Graphenated Carbon Nanotube Based MEMS Supercapacitors. <i>ECS Meeting Abstracts</i> , 2022, MA2022-01, 638-638.	0.0	0